

Triac Medium Power Use

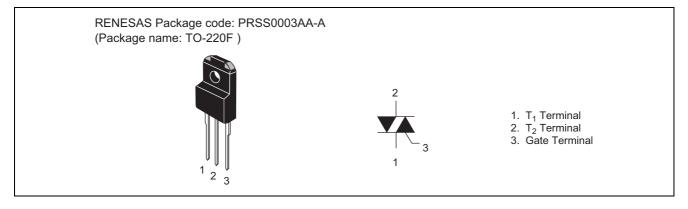
> REJ03G1557-0100 Rev.1.00 Jul 06, 2007

Features

- $I_{T(RMS)}$: 3 A
- V_{DRM} : 800 V (Tj = 125°C)
- I_{FGTI} , I_{RGTI} , I_{RGTIII} : 30 mA
- Viso : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized: Yellow Card No. E223904 File No. E80271

Outline



Applications

Washing machine, inversion operation of capacitor motor, and other general controlling devices

Maximum Ratings

| Parameter | Symbol | Voltage class | Unit | Conditions |
|--|------------------|---------------|------|------------|
| Falalleter | | 14 | Onic | |
| Repetitive peak off-state voltage ^{Note1} | V _{DRM} | 800 | V | Tj = 125°C |
| | | 700 | V | Tj = 150°C |
| Non-repetitive peak off-state voltage ^{Note1} | V _{DSM} | 840 | V | |

BCR3PM-14LG

| Parameter | Symbol | Ratings | Unit | Conditions |
|--------------------------------|----------------------|--------------|------------------|---|
| RMS on-state current | I _{T (RMS)} | 3.0 | A | Commercial frequency, sine full wave 360° conduction, Tc = 130°C |
| Surge on-state current | I _{TSM} | 30 | A | 60Hz sinewave 1 full cycle, peak value, non-repetitive |
| I ² t for fusing | l ² t | 3.7 | A ² s | Value corresponding to 1 cycle of half wave 60Hz, surge on-state current |
| Peak gate power dissipation | P _{GM} | 5 | W | |
| Average gate power dissipation | P _{G (AV)} | 0.5 | W | |
| Peak gate voltage | V _{GM} | 10 | V | |
| Peak gate current | I _{GM} | 2 | А | |
| Junction temperature | Tj | - 40 to +150 | °C | |
| Storage temperature | Tstg | - 40 to +150 | °C | |
| Mass | _ | 2.0 | g | Typical value |
| Isolation voltage | Viso | 2000 | V | Ta = 25°C, AC 1 minute, T ₁ • T ₂ • G terminal to case |

Notes: 1. Gate open.

Electrical Characteristics

| Parameter | | Symbol | Min. | Тур. | Max. | Unit | Test conditions |
|--|-----|-----------------------|---------|------|------|------|--|
| Repetitive peak off-state current | | I _{DRM} | — | — | 2.0 | mA | Tj = 150°C, V _{DRM} applied |
| On-state voltage | | V _{TM} | - | — | 1.6 | V | $Tc = 25^{\circ}C$, $I_{TM} = 4.5 A$, Instantaneous measurement |
| Gate trigger voltage ^{Note2} | Ι | V_{FGTI} | — | _ | 1.5 | V | $Tj=25^{\circ}C,\ V_D=6\ V,\ R_L=6\ \Omega,$ |
| | II | V _{rgti} | — | — | 1.5 | V | R _G = 330 Ω |
| | III | V _{RGTIII} | — | — | 1.5 | V | |
| Gate trigger current ^{Note2} | Ι | I_{FGTI} | _ | _ | 30 | mA | $Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$ |
| | II | I _{RGTI} | — | — | 30 | mA | R _G = 330 Ω |
| | III | I _{RGTIII} | — | — | 30 | mA | |
| Gate non-trigger voltage | | V_{GD} | 0.2/0.1 | _ | | V | $Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$ |
| Thermal resistance | | R _{th (j-c)} | — | _ | 5.2 | °C/W | Junction to case ^{Note3} |
| Critical-rate of rise of off-staticommutating voltage ^{Note4} | te | (dv/dt)c | 5/1 | — | — | V/µs | Tj = 125°C/150°C |

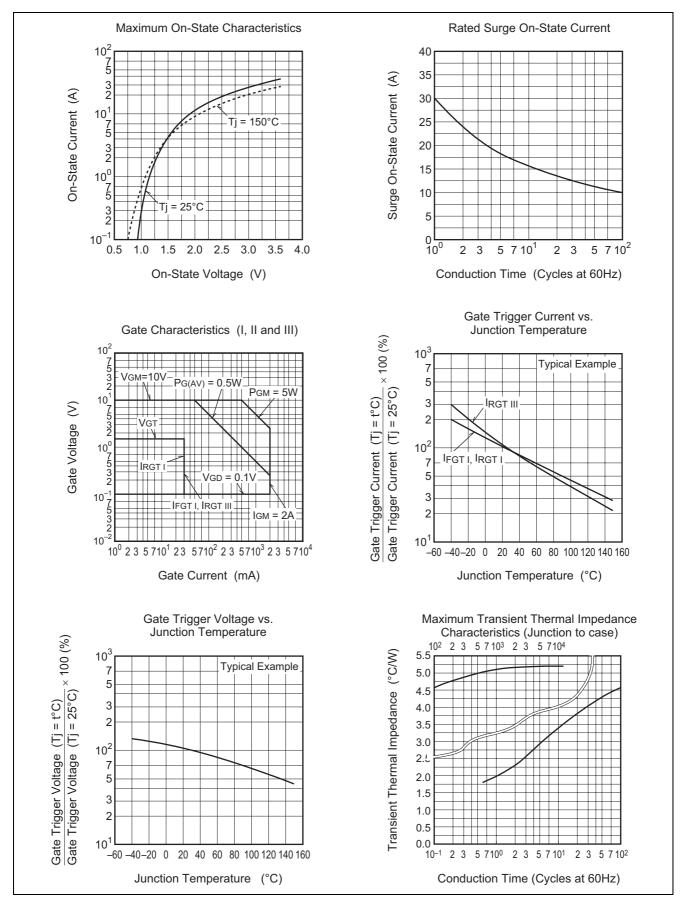
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

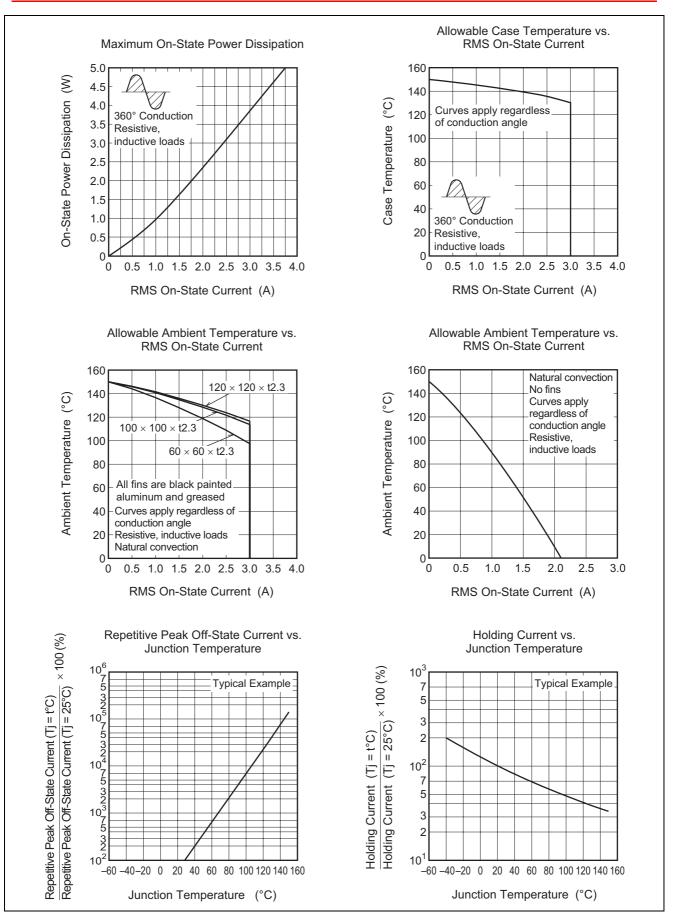
3. The contact thermal resistance $R_{th (c-f)}$ in case of greasing is 0.5°C/W.

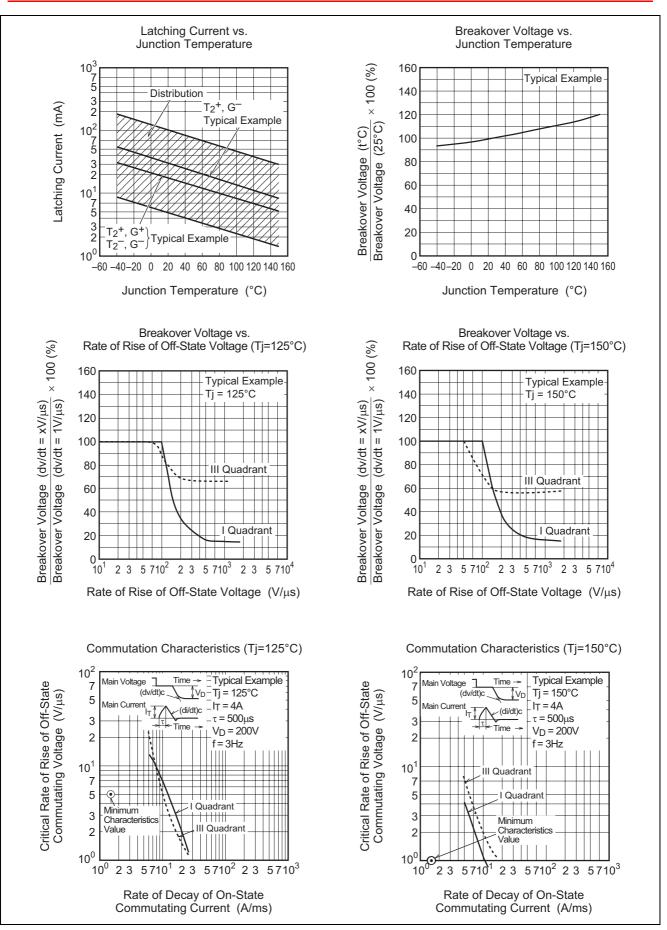
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

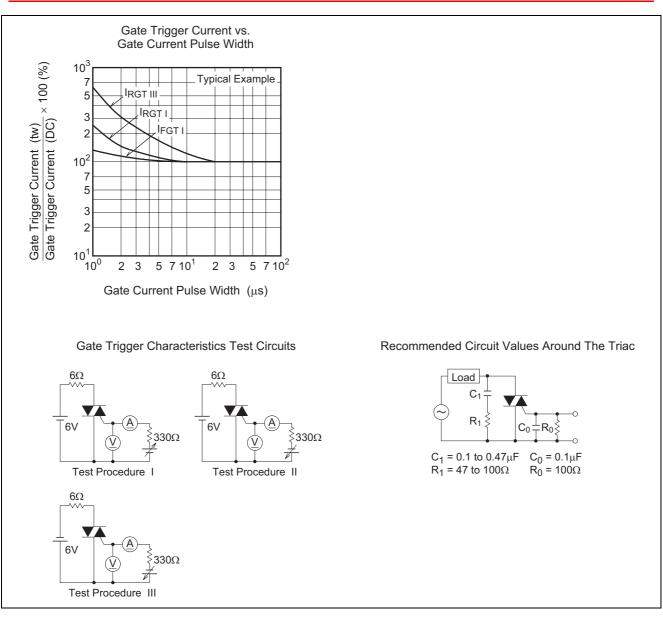
| Test conditions | Commutating voltage and current waveforms (inductive load) | | |
|--|---|--|--|
| 1. Junction temperature Tj = 125°C/150°C | Supply Voltage → Time | | |
| Rate of decay of on-state commutating current (di/dt)c = -1.5 A/ms | Main Current → Time | | |
| 3. Peak off-state voltage V _D = 400 V | Main VoltageTime (dv/dt)c V _D | | |

Performance Curves

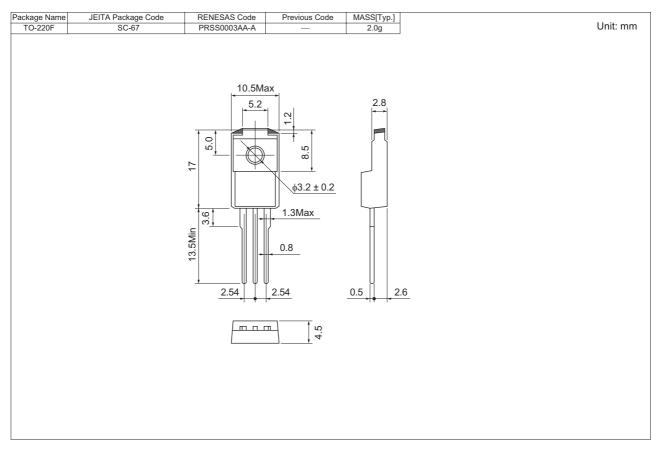








Package Dimensions



Order Code

| Lead form | Standard packing | Quantity | Standard order code | Standard order code example |
|---------------|-------------------------|----------|-------------------------------|--------------------------------|
| Straight type | Vinyl sack | 100 | Type name | BCR3PM-14LG |
| Lead form | Plastic Magazine (Tube) | 50 | Type name – Lead forming code | BCR3PM-14LG-A8 |

Note : Please confirm the specification about the shipping in detail.

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